



## 17 $\Omega$ , +12 V / ± 5 V / +5 V / +3 V, 8-Ch / Dual 4-Ch High Performance Analog Multiplexers

## DESCRIPTION

DG408LE, DG409LE The are monolithic analog multiplexers / demultiplexers designed to operate on single and dual supplies. Single supply voltage ranges from 3 V to 16 V while dual supply operation is recommended with  $\pm$  3 V to  $\pm$  8 V.

The DG408LE is an 8 channel single-ended analog multiplexer designed to connect one of eight inputs to a common output as determined by a 3 bit binary address (A<sub>0</sub>, A<sub>1</sub>, A<sub>2</sub>). The DG409LE is a dual 4 channel differential analog multiplexer designed to connect one of four differential inputs to a common dual output as determined by its 2 bit binary address (A<sub>0</sub>, A<sub>1</sub>). Break-before-make switching action to protect against momentary crosstalk between adjacent channels.

An on channel conducts current equally well in both directions. In the off state each channel blocks voltages up to the power supply rails. An enable (EN) function allows the user to reset the multiplexer / demultiplexer to all switches off for stacking several devices. All control inputs, address (Ax) and enable (EN) are TTL compatible over the full specified operating temperature range.

The DG408LE, DG409LE feature low on-resistance, fast switching time, and low leakage. They are ideal for data acquisition, control and automation, test instrument, and healthcare products. The DG408LE, DG409LE has an internal regulator powers the logic circuit. Such design reduces device power consumption and makes them ideal for battery operated applications.

The DG408LE, DG409LE are available in TSSOP16, SOIC16, and QFN16 packages.

## **FEATURES**

- Pin-for-pin compatibility with DG408, DG409, and DG508, DG509
- 3 V to 16 V single supply or ± 3 V to ± 8 V dual supply operation
- Low power consumption: 6 μA/max., EN = Vx = 5 V
- Lower on-resistance: R<sub>DS(on)</sub> 17 Ω typ.
- Fast switching: t<sub>ON</sub> 55 ns, t<sub>OFF</sub> 36 ns
- · Break-before-make guaranteed
- Low leakage: I<sub>S(OFF)</sub> 1 nA max.
- TTL, CMOS, LV logic (3 V) compatible
- -99 dB off-isolation and -98 dB crosstalk at 100 kHz
- Low parasitic capacitances: C<sub>S(OFF)</sub> = 5.5 pF  $C_{D(ON)} = 35 \text{ pF} (DG408 \text{LE})$
- ESD Protection:
  - ± 2.5 kV human body model
  - ± 100 V machine model
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

#### Note

This datasheet provides information about parts that are RoHS-compliant and / or parts that are non-RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details.

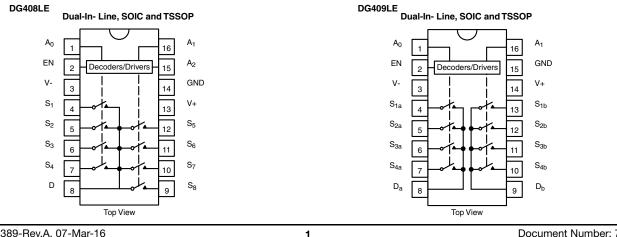
### BENEFITS

- High accuracy
- Single and dual power rail capacity
- Wide operating voltage range
- Simple logic interface

#### APPLICATIONS

- Automatic test equipment
- Data acquisition systems
- Meters and instruments
- Medical and healthcare systems
- Communication systems
- Audio and video signal routing
- Relav replacement
- Battery powered systems
- Computer peripherals
- · Audio and video signal routing

### FUNCTIONAL BLOCK DIAGRAMS AND PIN CONFIGURATIONS



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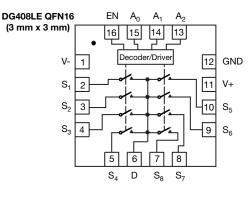
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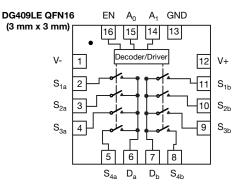
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## **QFN OUTLINE**





TRUTH TABLE (DG408LE)									
A <sub>2</sub>	<b>A</b> <sub>1</sub>	A <sub>0</sub>	EN	ON SWITCH					
Х	Х	Х	0	None					
0	0	0	1	1					
0	0	1	1	2					
0	1	0	1	3					
0	1	1	1	4					
1	0	0	1	5					
1	0	1	1	6					
1	1	0	1	7					
1	1	1	1	8					

TRUTH TABLE (DG409LE)								
A <sub>1</sub>	A <sub>0</sub>	EN	ON SWITCH					
Х	Х	0	None					
0	0	1	1					
0	1	1	2					
1	0	1	3					
1	1	1	4					

#### Note

• For low and high voltage levels for V<sub>AX</sub> and V<sub>EN</sub> consult "Digital Control" parameters for specific V+ operation.

ORDERING INFORMATION									
TEMP. RANGE	CONFIGURATION	PACKAGE	PART NUMBER	MIN. ORDER / PACK. QUANTITY					
		16-pin TSSOP	DG408LEDQ-GE3	Tube 360 units					
		10-pin 1330F	DG408LEDQ-T1-GE3	Tape and reel, 3000 units					
	8 Channel	16 pin SOIC	DG408LEDY-GE3	Tube 500 units					
	Single Ended DG408LE	16-pin SOIC	DG408LEDY-T1-GE3	Tape and reel, 2500 units					
-40 °C to +85 °C	DOHOULL	16-pin QFN (3 mm x 3 mm) Variation 2	DG408LEDN-T1-GE4	Tape and reel, 2500 units					
Lead-free			DG409LEDQ-GE3	Tube 360 units					
		16-pin TSSOP	DG409LEDQ-T1-GE3	Tape and reel, 3000 units					
	Dual 4 Channel	16-pin SOIC	DG409LEDY-GE3	Tube 500 units					
	Differential DG409LE	10-pin 3010	DG409LEDY-T1-GE3	Tape and reel, 2500 units					
	DUHUBLE	16-pin QFN (3 mm x 3 mm) Variation 2	DG409LEDN-T1-GE4	Tape and reel, 2500 units					

#### Note

• -T1 indicates tape and reel, -GE3 indicates lead (Pb)-free and RoHS-compliant, NO -GE3 indicates standard tin/lead finish.

Exposed pad of QFN package can be connected to GND, V-, or left floating.

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ABSOLUTE MAXIMUM RATINGS								
PARAMETER	LIMIT	UNIT						
V+ to V- <sup>e</sup>		18						
GND to V-		-18	V					
Digital Inputs <sup>a</sup> , V <sub>S</sub> , V <sub>D</sub>	(V-) - 0.3 to (V) + 0.3							
Current (any terminal)	30	mA						
Peak Current, S or D (pulsed at 1 ms, 10 %	100	- IIIA						
Storage Temperature	torage Temperature (D suffix)		°C					
	16-pin plastic TSSOP <sup>c</sup>	600						
Power Dissipation (package) <sup>b</sup>	16-pin narrow SOIC <sup>c</sup>	600	mW					
	16-pin miniQFN <sup>d</sup>	1385						
ESD Human Body Model (HBM); per ANSI /	2500	V						
Latch Up Current, per JESD78D	300	mA						

#### Notes

a. Signals on S<sub>X</sub>, D<sub>X</sub>, A<sub>X</sub>, or EN exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.

b. All leads soldered or welded to PC board.

c. Derate 8 mW/°C above 75 °C.

d. Derate 17.3 mW/°C above 70 °C

e. Also applies when V- = GND

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP. <sup>b</sup>	TYP. d		JFFIX o +85 °C	
		V+ = 12 V, ± 10 %, V- = 0 V V <sub>EN</sub> = 0.8 V or 2.4 V <sup>f</sup>			MIN. °	MAX. °	<b>U</b>
Analog Switch	<b>I</b>			I		I	•
Analog Signal Range <sup>e</sup>	V <sub>ANALOG</sub>		Full	-	0	12	V
Drain-Source	_	$V_{\rm D} = 10.8$ V, $V_{\rm D} = 2$ V or 9 V, $I_{\rm S} = 10$ mA	Room	17	-	23	
On-Resistance	R <sub>DS(on)</sub>	sequence each switch on	Full	-	-	27	
R <sub>DS(on)</sub> Matching Between Channels <sup>g</sup>	$\Delta R_{DS}$	$V_{\rm D} = 10.8 \text{ V}, V_{\rm D} = 2 \text{ V} \text{ or } 9 \text{ V}$	Room	1	-	3	Ω
On-Resistance Flatness	R <sub>FLAT(on)</sub>	I <sub>S</sub> = 10 mA	Room	3		6.5	
			Room	-	-1	1	
Switch Off Leakage	IS(off)	V <sub>EN</sub> = 0 V, V <sub>D</sub> = 11 V or 1 V	Full	-	-5	5	1
Current <sup>a</sup>		V <sub>S</sub> = 1 V or 11 V	Room	-	-1	1	
	I <sub>D(on)</sub>		Full	-	-5	5	nA
Channel On Leakage			Room	-	-1	1	
Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{S} = V_{D} = 1 V \text{ or } 11 V$	Full	-	-5	5	
Digital Control				1		1	
Logic High Input Voltage	V <sub>INH</sub>		Full	-	2.4	-	v
Logic Low Input Voltage	V <sub>INL</sub>		Full	-	-	0.8	v
Input Current <sup>a</sup>	I <sub>IN</sub>	V <sub>AX</sub> = V <sub>EN</sub> = 2.4 V or 0.8 V	Full	-	-1	1	μA
Dynamic Characteristics							
		V <sub>S1</sub> = 8 V, V <sub>S8</sub> = 0 V, (DG408LE)	Room	85	-	100	
Transition Time	t <sub>TRANS</sub>	$V_{S1b} = 8 V, V_{S4b} = 0 V, (DG409LE)$ see figure 2	Full	-	-	110	
Break-Before-Make Time		V <sub>S(all)</sub> = V <sub>DA</sub> = 5 V see figure 4	Room	34	1	-	ns
	t <sub>OPEN</sub>		Full	-	-	-	
			Room	55	-	72	
Enable Turn-On Time	t <sub>ON(EN)</sub>	$V_{AX} = 0 V, V_{S1} = 5 V (DG408LE)$	Full	-	-	82	
		V <sub>AX</sub> = 0 V, V <sub>S1b</sub> = 5 V (DG409LE) see figure 3	Room	36	-	47	
Enable Turn-Off Time	t <sub>OFF(EN)</sub>	see ligure 5	Full	-	-	50	
Charge Injection e (DG408LE)	_		Room	-11	-	-	_
Charge Injection <sup>e</sup> (DG409LE)	Q	$C_L$ = 1 nF, $V_{GEN}$ = 6 V, $R_{GEN}$ = 0 $\Omega$	Room	-10	-	-	рС
Off Isolation <sup>e, h</sup> (DG408LE)			Room	-99	_	_	
Off Isolation <sup>e, h</sup> (DG409LE)	OIRR		Room	-87	-	_	
Crosstalk <sup>e</sup> (DG408LE)		f = 100 kHz, $R_L = 50 \Omega$	Room	-98	-	_	dB
Crosstalk <sup>e</sup> (DG409LE)	X <sub>TALK</sub>		Room	-109	-	-	-
Source Off Capacitance e (DG408LE)			Room	5.5	-	-	
Source Off Capacitance <sup>e</sup> (DG409LE)	C <sub>S(off)</sub>	f = 1 MHz, $V_S$ = 0 V, $V_{EN}$ = 0 V	Room	5.5	-	-	
Drain Off Capacitance <sup>e</sup> (DG408LE)			Room	25	-	-	
Drain Off Capacitance <sup>e</sup> (DG409LE)	C <sub>D(off)</sub>	f = 1 MHz, V <sub>D</sub> = 2.4 V, V <sub>EN</sub> = 0 V	Room	13.5	-	-	рF
Drain On Capacitance (DG408LE)	Cart	f = 1 MHz, V <sub>D</sub> = 0 V, V <sub>EN</sub> = 2.4 V	Room	35	-	-	
Drain On Ćapacitance <sup>e</sup> (DG409LE)	C <sub>D(on)</sub>	(DG409LE only)	Room	23.5	-	-	
Power Supplies	1			1		1	1
Power Supply Range	V+			-	3	12	V
Power Supply Current	l+	$V_{EN} = V_A = 0 V \text{ or } 5 V$	Room	3.5		6	μA

#### Notes

a. Leakage parameters are guaranteed by worst case test condition and not subject to production test.

b. Room = 25 °C, Full = as determined by the operating temperature suffix.

c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

d. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

e. Guaranteed by design, not subject to production test.

f.  $V_{IN}$  = input voltage to perform proper function.

g.  $\Delta R_{DS(on)} = R_{DS(on)} \max$ . -  $R_{DS(on)} \min$ .

h. Worst case isolation occurs on Channel 4 do to proximity to the drain pin.

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SPECIFICATIONS	(Dual Sup	ply V+ = 5 V, V - = -5 V)						
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP. <sup>b</sup>	TYP.d	D SU -40 °C te	UNIT		
		V+ = 5 V, ± 10 %, V- = -5 V V <sub>EN</sub> = 0.6 V or 2.4 V <sup>f</sup>			MIN. c	MAX. c		
Analog Switch								
Analog Signal Range <sup>e</sup>	V <sub>ANALOG</sub>		Full	-	-5	5	V	
Drain-Source	Baar	$V_{D} = \pm 3.5 \text{ V}, \text{ I}_{S} = 10 \text{ mA}$	Room	15	-	25	Ω	
On-Resistance	R <sub>DS(on)</sub>	sequence each switch on	Full	-	-	30	52	
	la con		Room	-	-1	1		
Switch Off Leakage	I <sub>S(off)</sub>	V+ = 5.5, V- = 5.5 V	Full	-	-5	5		
Current <sup>a</sup>		$V_{EN} = 0 \text{ V}, V_{D} = \pm 4.5 \text{ V}, V_{S} = \pm 4.5 \text{ V}$	Room	-	-1	1	nA	
	I <sub>D(off)</sub>		Full	-	-5	5	ПА	
Channel On Leakage		V+ = 5.5 V, V- = -5.5 V	Room	-	-1	1		
Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{EN}$ = 2.4 V, $V_{D}$ = $\pm$ 4.5 V, $V_{S}$ = $\pm$ 4.5 V	Full	-	-5	5		
Digital Control						•	•	
Logic High Input Voltage	V <sub>INH</sub>		Full	-	2.4	-	v	
Logic Low Input Voltage	V <sub>INL</sub>		Full	-	-	0.6	v	
Input Current <sup>a</sup>	I <sub>IN</sub>	$V_{AX} = V_{EN} = 2.4 \text{ V or } 0.6 \text{ V}$	Full	-	-1	1	μA	
<b>Dynamic Characteristics</b>	;							
		$V_{S1} = 3.5 \text{ V}, V_{S8} = -3.5 \text{ V}, (DG408LE)$	Room	87	-	100	_	
Transition Time	t <sub>TRANS</sub>	$V_{S1b} = 3.5 \text{ V}, V_{S4b} = -3.5 \text{ V}, (DG409LE)$ see figure 2	Full	-	-	120		
Break-Before-Make Time	+	$V_{S(all)} = V_{DA} = 3.5 V$	Room	84	1	-		
Dieak-Deloie-Iviake Time	topen	see figure 4	Full	-	-	-	ns	
Enable Turn-On Time	+		Room	58	-	73		
Enable rum-On nine	t <sub>ON(EN)</sub>	$V_{AX} = 0 V, V_{S1} = 3.5 V (DG408LE)$	Full	-	-	80	-	
Enable Turn Off Time		$V_{AX} = 0 V, V_{S1b} = 3.5 V (DG409LE)$ see figure 3	Room	31	-	46		
Enable Turn-Off Time	t <sub>OFF(EN)</sub>		Full	-	-	51	1	
Source Off Capacitance <sup>e</sup> (DG408LE)			Room	6	-	-		
Source Off Capacitance <sup>e</sup> (DG409LE)	C <sub>S(off)</sub>	f = 1 MHz, $V_S$ = 0 V, $V_{EN}$ = 0 V	Room	5.5	-	-		
Drain Off Capacitance <sup>e</sup> (DG408LE)			Room	26	-	-	~ =	
Drain Off Capacitance <sup>e</sup> (DG409LE)	C <sub>D(off)</sub>	f = 1 MHz, $V_D$ = 0 V, $V_{EN}$ = 0 V	Room	14	-	-	- pF	
Drain On Capacitance <sup>e</sup> (DG408LE)			Room	36	-	-		
Drain On Capacitance <sup>e</sup> (DG409LE)	C <sub>D(on)</sub>	f = 1 MHz, V <sub>D</sub> = 0 V, V <sub>EN</sub> = 2.4 V	Room	24	-	-	1	

#### Notes

a. Leakage parameters are guaranteed by worst case test condition and not subject to production test.

b. Room = 25 °C, full = as determined by the operating temperature suffix.

c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.

d. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

e. Guaranteed by design, not subject to production test.

f.  $V_{IN}$  = input voltage to perform proper function.

g.  $\Delta R_{DS(on)} = R_{DS(on)} \max$ . -  $R_{DS(on)} \min$ .

h. Worst case isolation occurs on channel 4 do to proximity to the drain pin.

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SPECIFICATIONS (S	Single Sup	pply 5 V)							
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP. <sup>b</sup>	TYP. <sup>d</sup>		JFFIX o +85 °C	UNIT		
		V+ = 5 V, ± 10 %, V- = 0 V V <sub>EN</sub> = 0.6 V or 2.4 V <sup>f</sup>			MIN. °	MAX. °			
Analog Switch									
Analog Signal Range <sup>e</sup>	VANALOG		Full	-	0	5	V		
Drain-Source	R <sub>DS(on)</sub>	$V_{+} = 4.5 V$ , $V_{D}$ or $V_{S} = 1 V$ or $3.5 V$ ,	Room	28	-	36			
On-Resistance	TDS(on)	I <sub>S</sub> = 5 mA	Full	-	-	41			
R <sub>DS(on)</sub> Matching Between Channels <sup>g</sup>	$\Delta R_{DS}$	$V_{+} = 4.5 V, V_{D} = 1 V \text{ or } 3.5 V,$	Room	1	-	3	Ω		
On-Resistance Flatness	R <sub>FLAT(on)</sub>	I <sub>S</sub> = 5 mA	Room	-	-	4			
	I <sub>S(off)</sub>		Room	-	-1	1			
Switch Off Leakage	<sup>1</sup> S(0ff)	$V$ + = 5.5 V, $V_S$ = 1 V or 4 V	Full	-	-5	5			
Current <sup>a</sup>		$V_D = 4 V \text{ or } 1 V$	Room	-	-1	1	nA		
	I <sub>D(off)</sub>		Full	-	-5	5	114		
Channel On Leakage		$V$ + = 5.5 V, $V_D$ = $V_S$ = 1 V or 4 V	Room	-	-1	1			
Current <sup>a</sup>	I <sub>D(on)</sub>	sequence each switch on	Full	-	-5	5			
Digital Control									
Logic High Input Voltage	V <sub>INH</sub>	V+ = 5 V	Full	-	2.4	-	V		
Logic Low Input Voltage	V <sub>INL</sub>	V+ = 5 V	Full	-	-	0.6			
Input Current <sup>a</sup>	I <sub>IN</sub>	$V_{AX} = V_{EN} = 2.4 \text{ V or } 0.6 \text{ V}$	Full	-	-1	1	μA		
<b>Dynamic Characteristics</b>									
			Room	113	-	135			
Transition Time	t <sub>TRANS</sub>		Full	-	-	165			
Break-Before-Make Time	+	$V_{S(all)} = V_{DA} = 3.5 \text{ V},$	Room	75	1	-			
break-beiore-wake time	t <sub>OPEN</sub>	see figure 4	Full	-	-	-	ns		
Enable Turn-On Time	t <sub>ON(EN)</sub>	+	÷		Room	77	-	89	110
Enable Turn-On Time		$V_{AX} = 0 V, V_{S1} = 3.5 V (DG408LE)$	Full	-	-	110			
Enchle Turn Off Time		V <sub>AX</sub> = 0 V, V <sub>S1b</sub> = 3.5 V (DG409LE) see figure 3	Room	43	-	50	1		
Enable Turn-Off Time	t <sub>OFF(EN)</sub>	<b>3</b>	Full	-	-	53			
Charge Injection e (DG408LE)	0		Room	-2	-	-			
Charge Injection e (DG409LE)	Q	$C_L = 1 \text{ nF}, R_{GEN} = 0 \Omega, V_{GEN} = 2.5 \text{ V}$	Room	-2	-	-	рС		
Off Isolation e, h (DG408LE)			Room	-100	-	-			
Off Isolation e, h (DG409LE)	OIRR		Room	-83	-	-			
Crosstalk <sup>e</sup> (DG408LE)	V	f = 100 kHz, $R_L$ = 50 $\Omega$	Room	-101	-	-	dB		
Crosstalk <sup>e</sup> (DG409LE)	X <sub>TALK</sub>		Room	-108	-	-			
Source Off Capacitance <sup>e</sup> (DG408LE)	0		Room	6.5	-	-			
Source Off Capacitance <sup>e</sup> (DG409LE)	C <sub>S(off)</sub>	f = 1 MHz, $V_S$ = 0 V, $V_{EN}$ = 0 V	Room	6.5	-	-			
Drain Off Capacitance <sup>e</sup> (DG408LE)		f = 1 MHz, V <sub>D</sub> = 0 V, V <sub>EN</sub> = 0 V	Room	30	-	-	ъF		
Drain Off Capacitance <sup>e</sup> (DG409LE)	C <sub>D(off)</sub>	$v = v w v v_{\rm EN} = 0 v$	Room	16	-	-	pF		
Drain On Ćapacitance <sup>e</sup> (DG408LE)	C <sub>D(on)</sub>	f = 1 MHz, V <sub>D</sub> = 0 V, V <sub>EN</sub> = 2.4 V	Room	40	-	-			
Drain On Capacitance <sup>e</sup> (DG409LE)	℃D(on)	$V \rightarrow V$ , $V = 0$ , $V = 2.4$ V	Room	26.5	-	-			

#### Notes

a. Leakage parameters are guaranteed by worst case test condition and not subject to production test.

b. Room =  $25 \,^{\circ}$ C, full = as determined by the operating temperature suffix.

c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

d. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

e. Guaranteed by design, not subject to production test.

f.  $V_{IN}$  = input voltage to perform proper function.

g.  $\Delta R_{DS(on)} = R_{DS(on)} \text{ max.} - R_{DS(on)} \text{ min.}$ 

h. Worst case isolation occurs on channel 4 do to proximity to the drain pin.

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SPECIFICATIONS (Single Supply 3 V)									
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP. <sup>b</sup>	TYP.d		JFFIX o +85 °C	UNIT		
	OTINDOL	V+ = 3 V, ± 10 %, V- = 0 V V <sub>EN</sub> = 0.4 V or 2 V <sup>f</sup>			MIN. °	MAX. °	UNIT		
Analog Switch									
Analog Signal Range <sup>e</sup>	V <sub>ANALOG</sub>		Full	-	0	3	V		
Drain-Source	<b>D</b>	$V_{+} = 2.7 V, V_{D} = 0.5 \text{ or } 2.2 V,$	Room	63	-	80	Ω		
On-Resistance	R <sub>DS(on)</sub>	I <sub>S</sub> = 5 mA	Full	-	-	92	52		
	1		Room	-	-1	1			
Switch Off Leakage	I <sub>S(off)</sub>	$V_{+} = 3.3 V, V_{S} = 2 \text{ or } 1 V, V_{D} = 1 \text{ or } 2 V$	Full	-	-5	5			
Current <sup>a</sup>		$v_{+} = 3.3 v, v_{S} = 2 01 v, v_{D} = 101 2 v$	Room	-	-1	1	~ ^		
	I <sub>D(off)</sub>		Full	-	-5	5	nA		
Channel On Leakage		$V_{+} = 3.3 V, V_{D} = V_{S} = 1 V \text{ or } 2 V$	Room	-	-1	1			
Current <sup>a</sup>	I <sub>D(on)</sub>	sequence each switch on	Full	-	-5	5			
Digital Control		· · · ·		•	•	•			
Logic High Input Voltage	V <sub>INH</sub>		Full	-	2	-	M		
Logic Low Input Voltage	V <sub>INL</sub>		Full	-	-	0.4	V		
Input Current <sup>a</sup>	I <sub>IN</sub>	$V_{AX} = V_{EN} = 2.4 \text{ V or } 0.4 \text{ V}$	Full	-	-1	1	μA		
Dynamic Characteristics		•		•		•			
			Room	211	-	275			
Transition Time	t <sub>TRANS</sub>		Full	-	-	300			
Break-Before-Make Time	tonnu	$V_{S(all)} = V_{DA} = 1.5 V,$	Room	209	1	-			
Dreak-Delore-Iviake Time	t <sub>OPEN</sub>	see figure 4	Full	-	-	-	ns		
Enchla Turn On Time	1		Room	125	-	150			
Enable Turn-On Time	t <sub>ON(EN)</sub>	$V_{AX} = 0 V, V_{S1} = 1.5 V (DG408LE)$	Full	-	-	180			
	1	V <sub>AX</sub> = 0 V, V <sub>S1b</sub> = 1.5 V (DG409LE) see figure 3	Room	45	-	75			
Enable Turn-Off Time	t <sub>OFF(EN)</sub>	Jan	Full	-	-	95			
Charge Injection <sup>e</sup> (DG408LE)	0		Room	0	-	-	- 0		
Charge Injection <sup>e</sup> (DG409LE)	Q	$C_L = 1 \text{ nF}, R_{GEN} = 0 \Omega, V_{GEN} = 1.5 \text{ V}$	Room	-0.4	-	-	рС		
Off Isolation e, h (DG408LE)	0100		Room	-90	-	-			
Off Isolation e, h (DG409LE)	OIRR		Room	-95	-	-			
Crosstalk e (DG408LE)		f = 100 kHz, $R_L = 50 \Omega$	Room	-95	-	-	dB		
Crosstalk e (DG409LE)	X <sub>TALK</sub>		Room	-93	-	-			
Source Off Capacitance e (DG408LE)	6		Room	7	-	-			
Source Off Capacitance <sup>e</sup> (DG409LE)	$C_{S(off)}$	f = 1 MHz, V <sub>S</sub> = 0 V, V <sub>EN</sub> = 0 V	Room	7	-	-			
Drain Off Capacitance <sup>e</sup> (DG408LE)	C <sub>D(off)</sub>	f = 1 MHz, V <sub>D</sub> = 0 V, V <sub>EN</sub> = 0 V	Room	33	-	-	pF		
Drain Off Capacitance e (DG409LE)	Ο(OΠ)		Room	18	-	-	<b>۲</b> '		
Drain On Capacitance <sup>e</sup> (DG408LE)	C <sub>D(on)</sub>	f = 1 MHz, V <sub>D</sub> = 0 V, V <sub>EN</sub> = 2 V	Room	43	-	-			
Drain On Capacitance <sup>e</sup> (DG409LE)	- D(01)	, , , , , , Lin	Room	28	-	-			

#### Notes

a. Leakage parameters are guaranteed by worst case test condition and not subject to production test.

b. Room = 25 °C, full = as determined by the operating temperature suffix.

c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

d. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

e. Guaranteed by design, not subject to production test.

f.  $V_{IN}$  = input voltage to perform proper function.

g.  $\Delta R_{DS(on)} = R_{DS(on)} \max$ . -  $R_{DS(on)} \min$ .

h. Worst case isolation occurs on channel 4 do to proximity to the drain pin.

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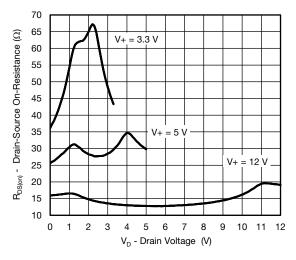
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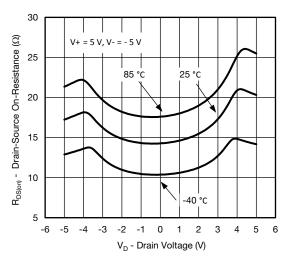
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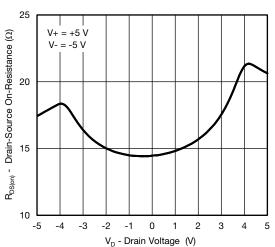
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



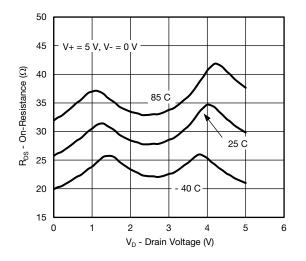
 $R_{DS(on)}\,vs.\,V_{D}$  and Power Supply



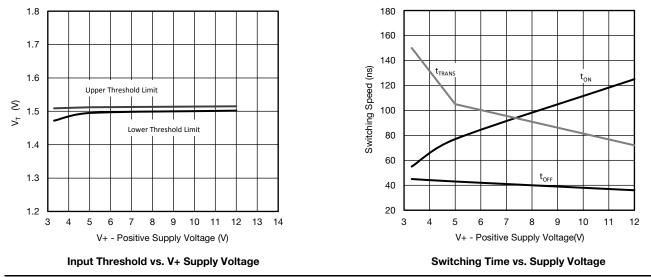
R<sub>DS(on)</sub> vs. V<sub>D</sub> and Temperature (Dual Supply)



R<sub>DS(on)</sub> vs. V<sub>D</sub> and Power Supply







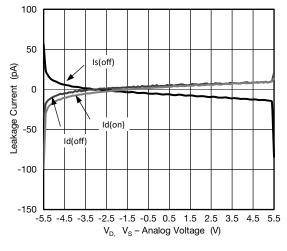
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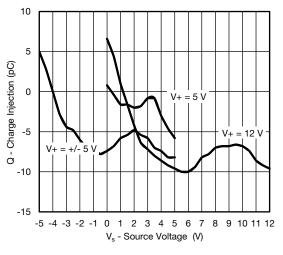
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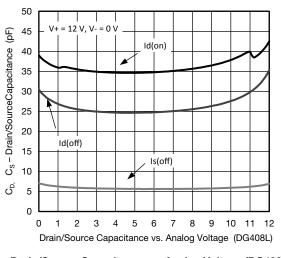
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Leakage Current vs. Analog Voltage



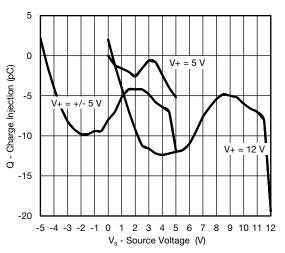
Charge Injection vs. Analog Voltage (DG409LE)



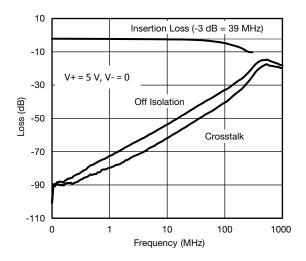
Drain/Source Capacitance vs. Analog Voltage (DG408LE)

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Charge Injection vs. Analog Voltage (DG408LE)



Insertion Loss, Off Isolation, and Crosstalk vs. Frequency



## SCHEMATIC DIAGRAM (Typical Channel)

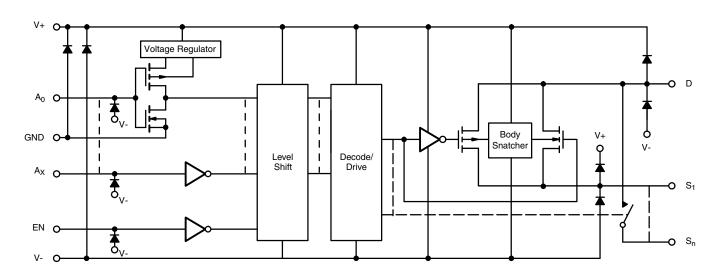
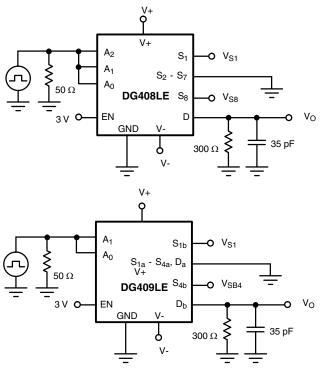
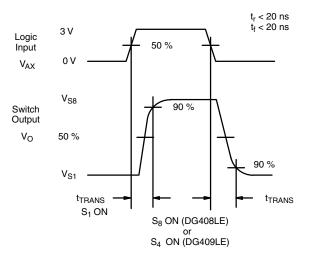


Fig. 1

### **TEST CIRCUITS**





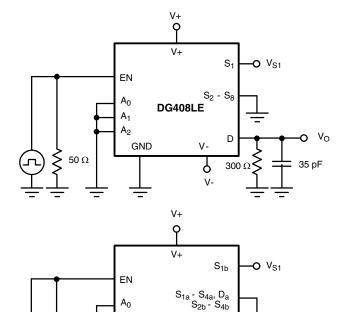


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**Vishay Siliconix** 

## **TEST CIRCUITS**



DG409LE

 $D_b$ 

<u>\_\_\_</u>300 Ω≶

V-

δ

V-

A<sub>1</sub>

50 Ω

Л

GND

\_

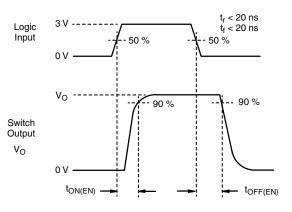


Fig. 3 - Enable Switching Time

 $V_{\mathsf{O}}$ 

0

35 pF

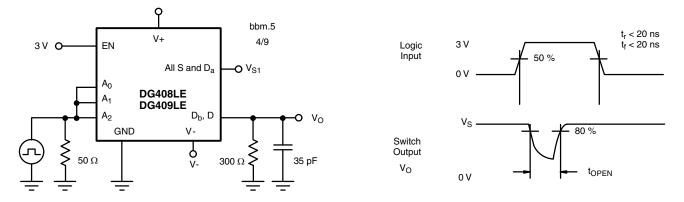


Fig. 4 - Break-Before-Make Interval

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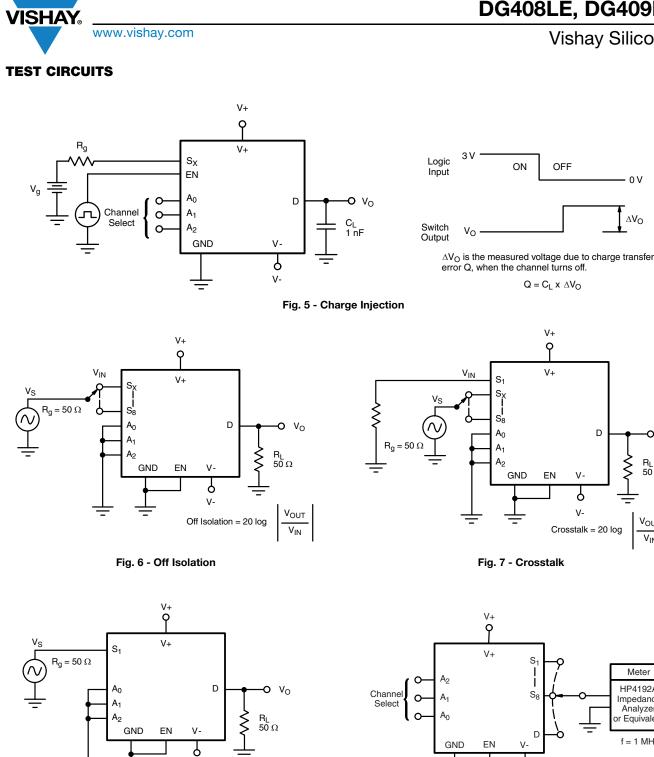


Fig. 9 - Source Drain Capacitance

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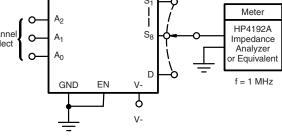
VOUT

VIN

Insertion Loss = 20 log

٧

Fig. 8 - Insertion Loss



DG408LE, DG409LE

**Vishay Siliconix** 

Vo

0

RL 50 Ω

VOUT

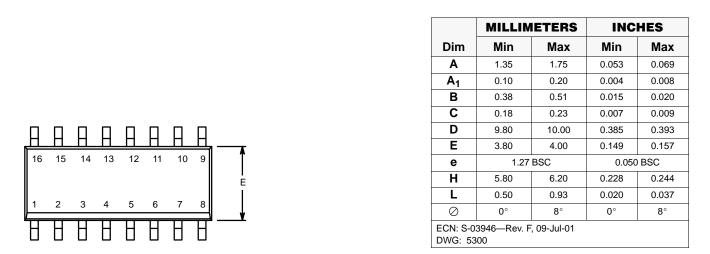
VIN

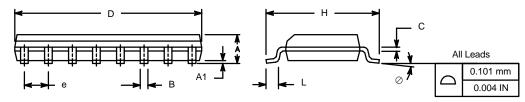


## Package Information Vishay Siliconix

SOIC (NARROW): 16-LEAD

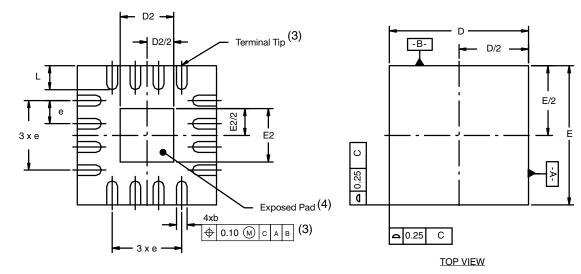
JEDEC Part Number: MS-012



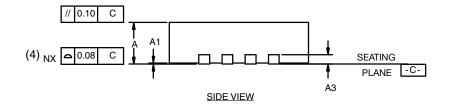




QFN-16 Lead (3 x 3)



BOTTOM VIEW



### Notes

<sup>(1)</sup> All dimensions are in millimeters.

<sup>(2)</sup> N is the total number of terminals.

<sup>(3)</sup> Dimension b applies to metallized terminal and is measured between 0.25 and 0.30 mm from terminal tip.

<sup>(4)</sup> Coplanarity applies to the exposed heat sink slug as well as the terminal.

<sup>(5)</sup> The pin #1 identifier may be either a mold or marked feature, it must be located within the zone indicated.

			VARIA	TION 1	DN 1				VARIATION 2			
DIM.	м	ILLIMETE	RS		INCHES		MILLIMETERS			INCHES		
	MIN.	NOM	MAX.	MIN.	NOM	MAX.	MIN.	NOM	MAX.	MIN.	NOM	MAX.
А	0.80	0.90	1.00	0.031	0.035	0.039	0.80	0.90	1.00	0.031	0.035	0.039
b	0.18	0.23	0.30	0.007	0.009	0.012	0.18	0.25	0.30	0.007	0.010	0.012
D	2.90	3.00	3.10	0.114	0.118	0.122	2.90	3.00	3.10	0.114	0.118	0.122
D2	1.00	1.15	1.25	0.039	0.045	0.049	1.50	1.70	1.80	0.059	0.067	0.071
E	2.90	3.00	3.10	0.114	0.118	0.122	2.90	3.00	3.10	0.114	0.118	0.122
E2	1.00	1.15	1.25	0.039	0.045	0.049	1.50	1.70	1.80	0.059	0.067	0.071
е		0.50 BSC			0.020 BSC	;	0.50 BSC			0.020 BSC		
L	0.30	0.40	0.50	0.012	0.016	0.020	0.30	0.40	0.50	0.012	0.016	0.020
ECN: T16-0233-Rev. D, 09-May-16 DWG: 5899												

Revision: 09-May-16

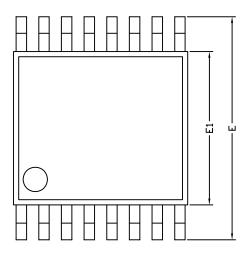
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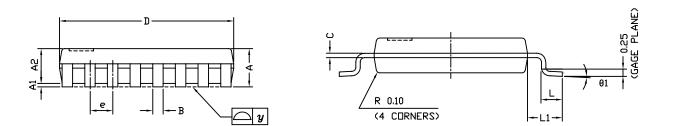


# Package Information

Vishay Siliconix

## TSSOP: 16-LEAD





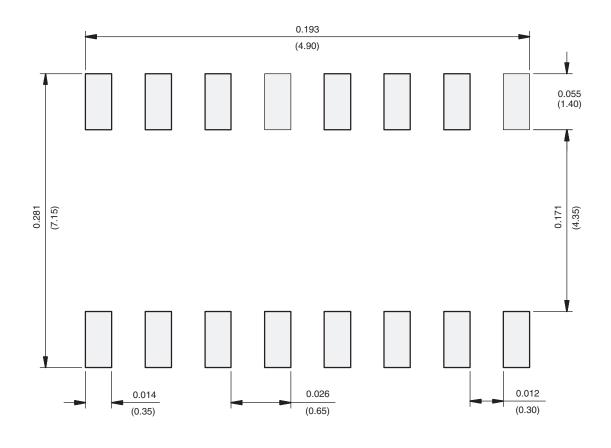
	DIMENSIONS IN MILLIMETERS								
Symbols	Min	Nom	Max						
A	-	1.10	1.20						
A1	0.05	0.10	0.15						
A2	-	1.00	1.05						
В	0.22	0.28	0.38						
С	-	0.127	-						
D	4.90	5.00	5.10						
E	6.10	6.40	6.70						
E1	4.30	4.40	4.50						
е	-	0.65	-						
L	0.50	0.60	0.70						
L1	0.90	1.00	1.10						
у	-	-	0.10						
θ1	0°	3°	6°						
ECN: S-61920-Rev. D, 23 DWG: 5624	-Oct-06								



**PAD** Pattern

Vishay Siliconix

### **RECOMMENDED MINIMUM PAD FOR TSSOP-16**



Recommended Minimum Pads Dimensions in inches (mm)

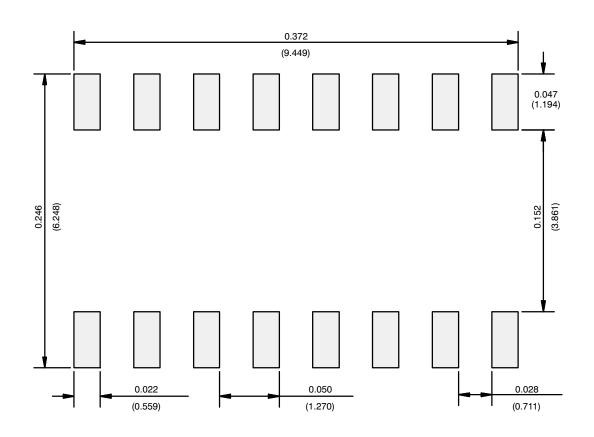
Revision: 02-Sep-11

# **Application Note 826**

Vishay Siliconix



## **RECOMMENDED MINIMUM PADS FOR SO-16**



Recommended Minimum Pads Dimensions in Inches/(mm)

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